

SKKH 273/18 E



SEMIPACK® 3

Thyristor / Diode Modules

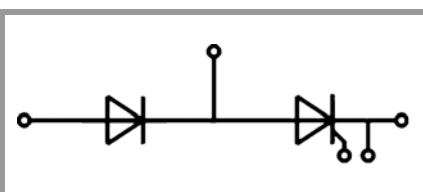
SKKH 273/18 E

Features*

- Industrial standard package
- Electrically insulated base plate
- Heat transfer through aluminum oxide ceramic insulated metal base plate
- Chip soldered on direct copper bonded Al₂O₃ ceramic
- UL recognition, file no. E63532

Typical Applications

- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)



SKKH

| Absolute Maximum Ratings | | | | |
|--------------------------|-------------------------|-------------------------|-------------|------------------|
| Symbol | Conditions | | Values | Unit |
| Chip | | | | |
| I _{T(AV)} | sinus 180° | T _c = 85 °C | 274 | A |
| | | T _c = 100 °C | 204 | A |
| I _{TSM} | 10 ms | T _j = 25 °C | 9000 | A |
| | | T _j = 130 °C | 8000 | A |
| i ² t | 10 ms | T _j = 25 °C | 405000 | A ² s |
| | | T _j = 130 °C | 320000 | A ² s |
| V _{RSM} | | | 1900 | V |
| V _{RRM} | | | 1800 | V |
| V _{DRM} | | | 1800 | V |
| (di/dt) _{cr} | T _j = 130 °C | | 130 | A/μs |
| (dv/dt) _{cr} | T _j = 130 °C | | 1000 | V/μs |
| T _j | | | -40 ... 130 | °C |
| Module | | | | |
| T _{stg} | | | -40 ... 125 | °C |
| V _{isol} | a.c.; 50 Hz; r.m.s. | 1 min | 3000 | V |
| | | 1 s | 3600 | V |

| Characteristics | | | | | | |
|-----------------------------------|--|------------|------|------|----------|------------------|
| Symbol | Conditions | | min. | typ. | max. | Unit |
| Chip | | | | | | |
| V _T | T _j = 25 °C, I _T = 750 A | | | | 1.6 | V |
| V _{T(TO)} | T _j = 130 °C | | | | 0.90 | V |
| r _T | T _j = 130 °C | | | | 0.92 | mΩ |
| I _{DD} ; I _{RD} | T _j = 130 °C, V _{DD} = V _{DRM} ; V _{RD} = V _{RRM} | | | | 100 | mA |
| t _{gd} | T _j = 25 °C, I _G = 1 A, di _G /dt = 1 A/μs | | | 1 | | μs |
| t _{gr} | V _D = 0.67 * V _{DRM} | | | 2 | | μs |
| t _q | T _j = 130 °C | | | 150 | | μs |
| I _H | T _j = 25 °C | | | 150 | 500 | mA |
| I _L | T _j = 25 °C, R _G = 33 Ω | | | 300 | 2000 | mA |
| V _{GT} | T _j = 25 °C, d.c. | | 2 | | | V |
| I _{GT} | T _j = 25 °C, d.c. | | 150 | | | mA |
| V _{GD} | T _j = 130 °C, d.c. | | | | 0.25 | V |
| I _{GD} | T _j = 130 °C, d.c. | | | | 10 | mA |
| R _{th(j-c)} | cont. | per chip | | | 0.104 | K/W |
| | | per module | | | 0.052 | K/W |
| R _{th(j-c)} | sin. 180° | per chip | | | 0.108 | K/W |
| | | per module | | | 0.054 | K/W |
| R _{th(j-c)} | rec. 120° | per chip | | | 0.122 | K/W |
| | | per module | | | 0.061 | K/W |
| Module | | | | | | |
| R _{th(c-s)} | chip | | | 0.08 | | K/W |
| | module | | | 0.04 | | K/W |
| M _s | to heatsink M5 | | 4.25 | | 5.75 | Nm |
| M _t | to terminals M8 | | 7.65 | | 10.35 | Nm |
| a | | | | | 5 * 9.81 | m/s ² |
| w | | | | 410 | | g |

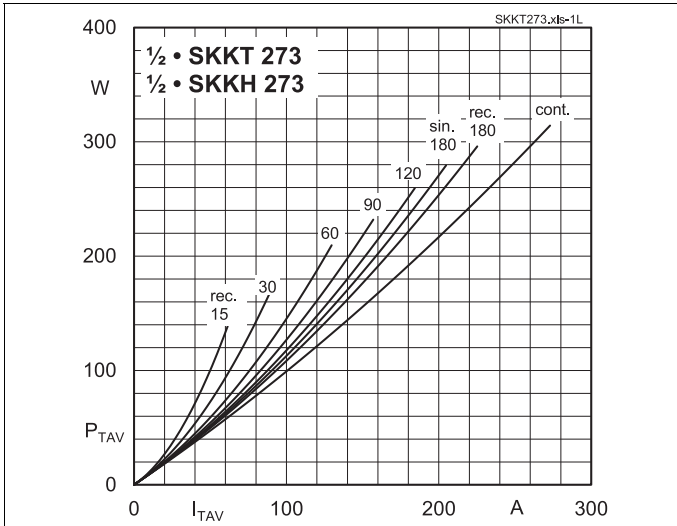


Fig. 1L: Power dissipation per thyristor/diode vs. on-state current

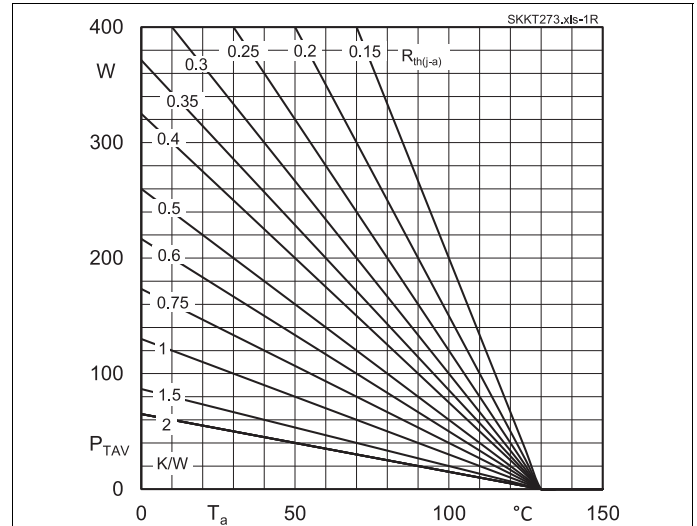


Fig. 1R: Power dissipation per thyristor/diode vs. ambient temperature

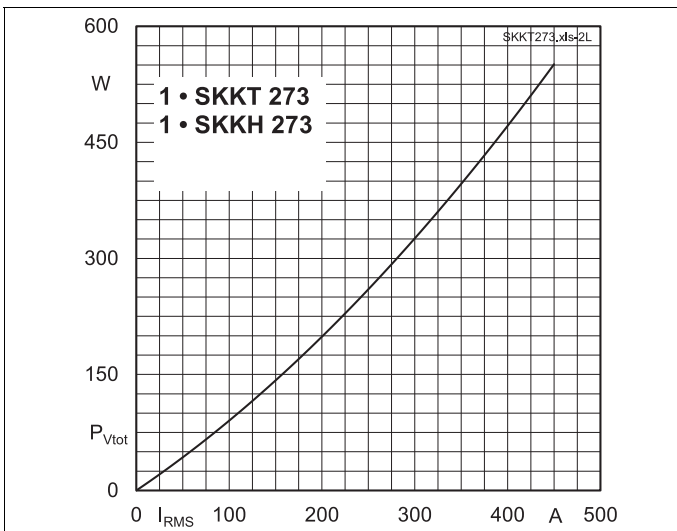


Fig. 2L: Power dissipation of one module vs. rms current

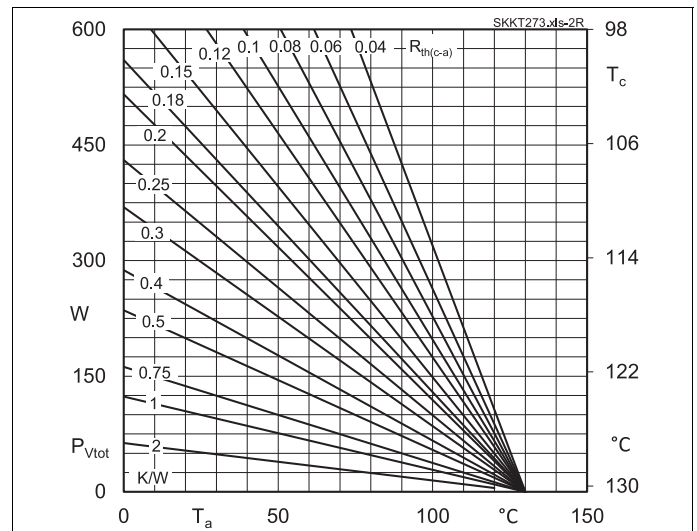


Fig. 2R: Power dissipation of one module vs. case temperature

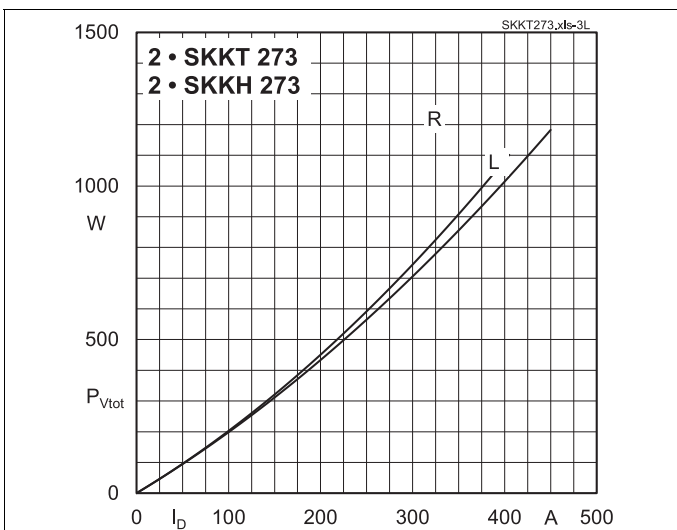


Fig. 3L: Power dissipation of two modules vs. direct current

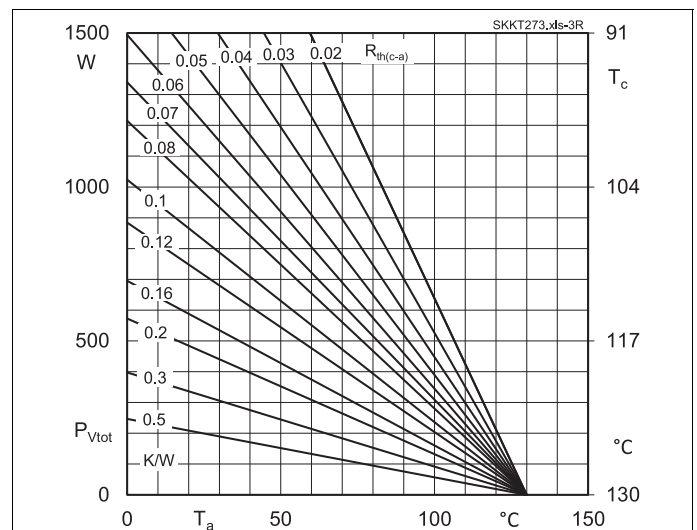


Fig. 3R: Power dissipation of two modules vs. case temperature

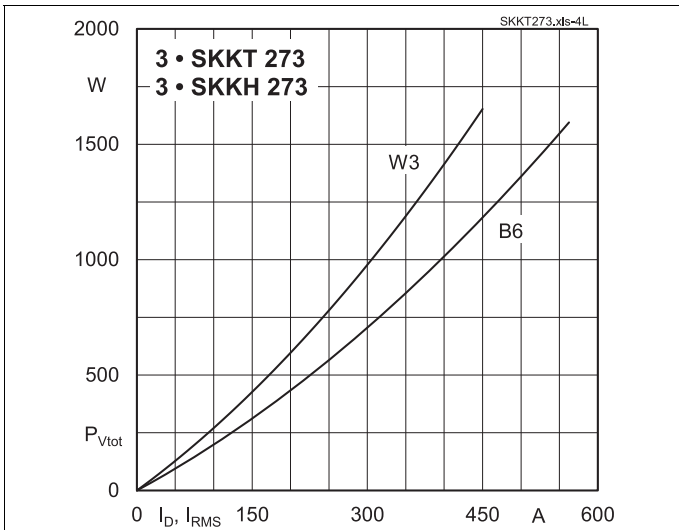


Fig. 4L: Power dissipation of three modules vs. direct and rms current

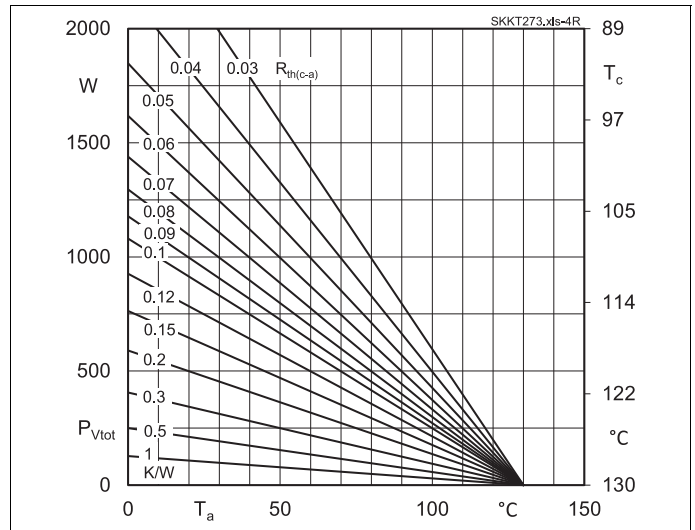


Fig. 4R: Power dissipation of three modules vs. case temperature

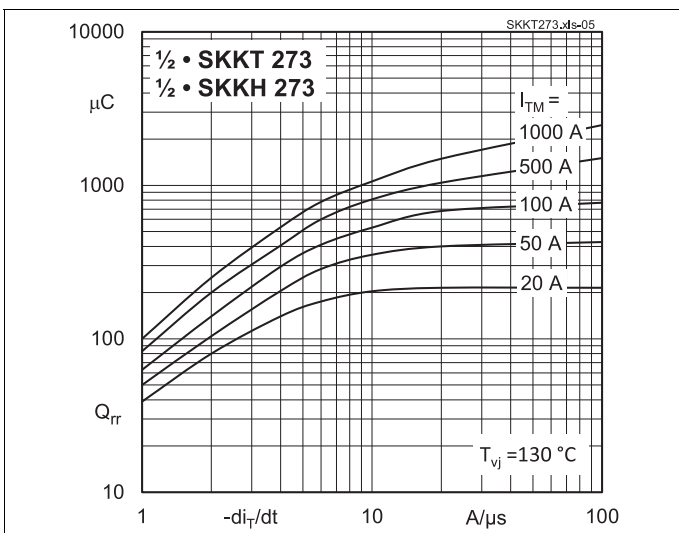


Fig. 5: Recovered charge vs. current decrease

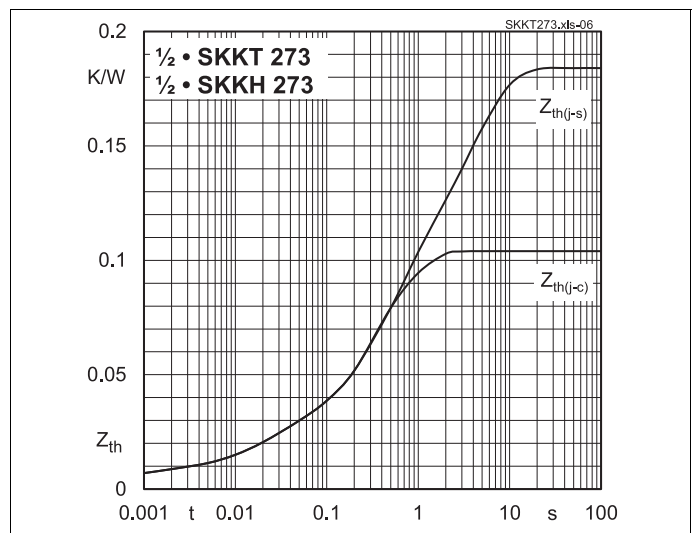


Fig. 6: Transient thermal impedance vs. time

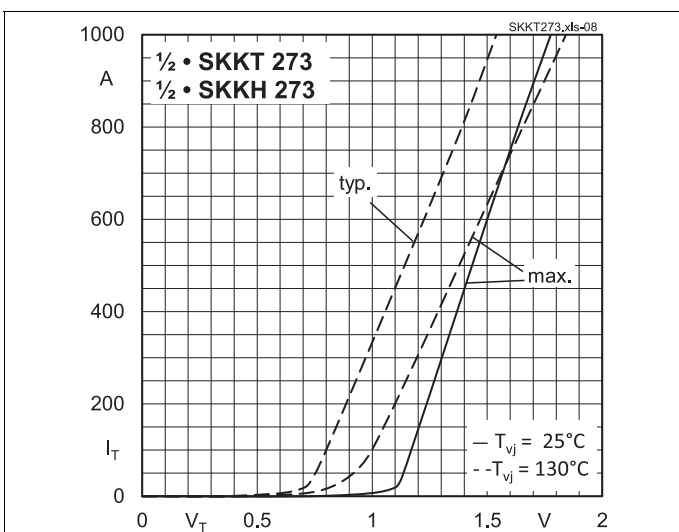


Fig. 7: On-state characteristics

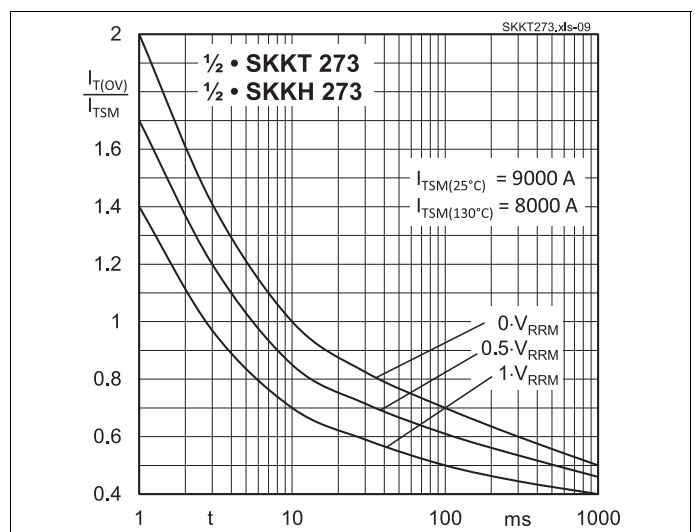


Fig. 8: Surge overload current vs. time

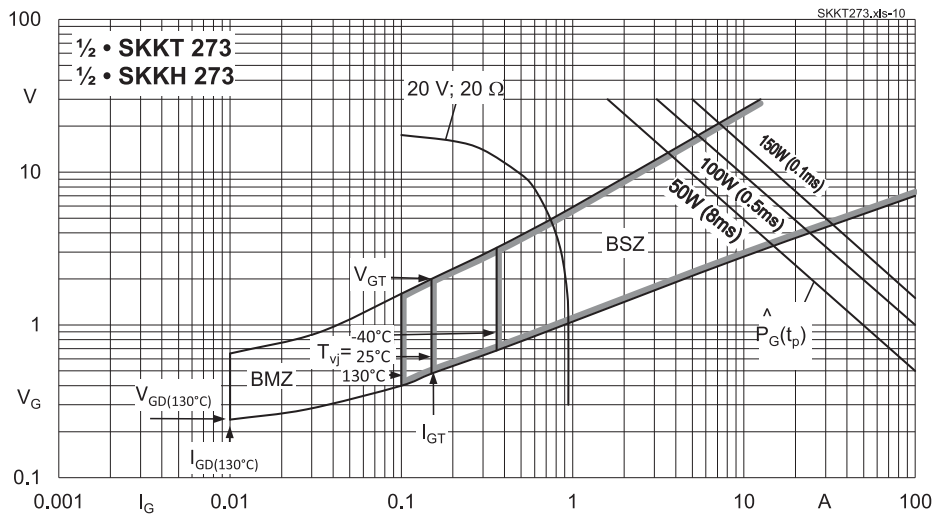
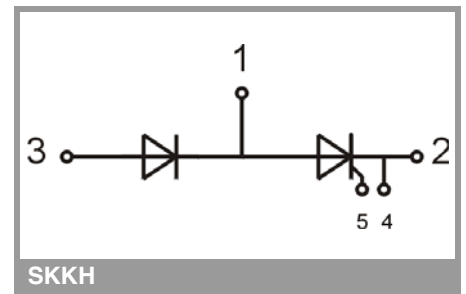
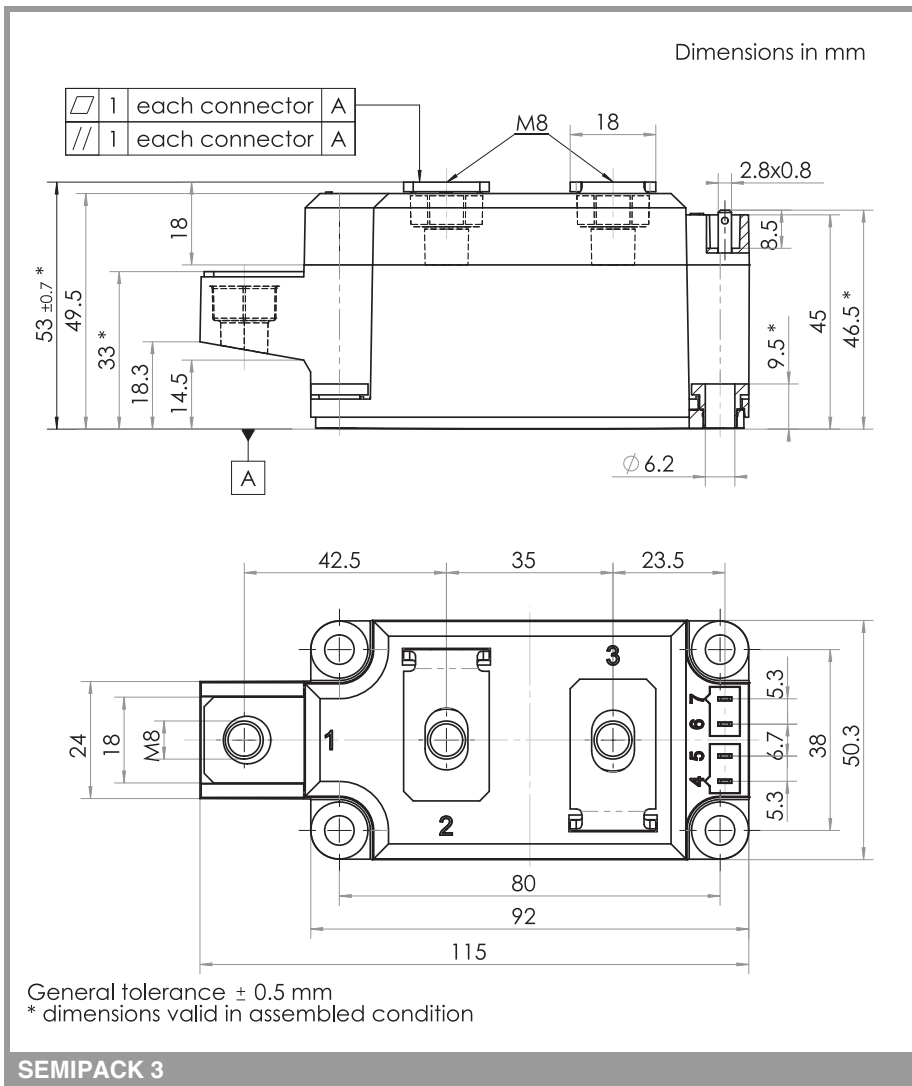


Fig. 9: Gate trigger characteristics



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

*IMPORTANT INFORMATION AND WARNINGS

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